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60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	$25m\Omega @ V_{GS} = 10V$	32A
60 V	$40m\Omega$ @ $V_{GS} = 4.5V$	25A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

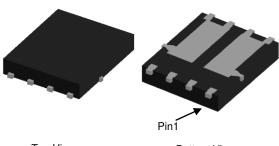
- Backlighting
- Power Management Functions
- DC-DC Converters

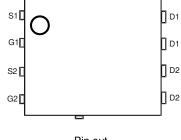
Features and Benefits

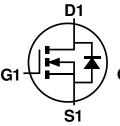
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Complaint Part is Available Under Separate Datasheet (DMNH6021SPDQ)

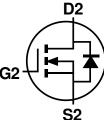
Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)









Top View Bottom View

Pin out
Top View Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging	
DMNH6021SPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 3. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking H6021SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 - 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_A = +25$ °C $T_A = +70$ °C	I _D	8.2 6.5	А
Continuous Drain Current (Note 7) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$		I _D	32 22	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	32	Α	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	35	Α	
Avalanche Energy, L = 0.1mH (Note 8)	Eas	64	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		P _D	1.5	W
Theymal Decistores, Junetica to Ambient (Note 5)		0	99	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	53	G/VV
Total Power Dissipation (Note 6)		P _D	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	54	°C/W
Thermal nesistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	27	
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	2.2	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

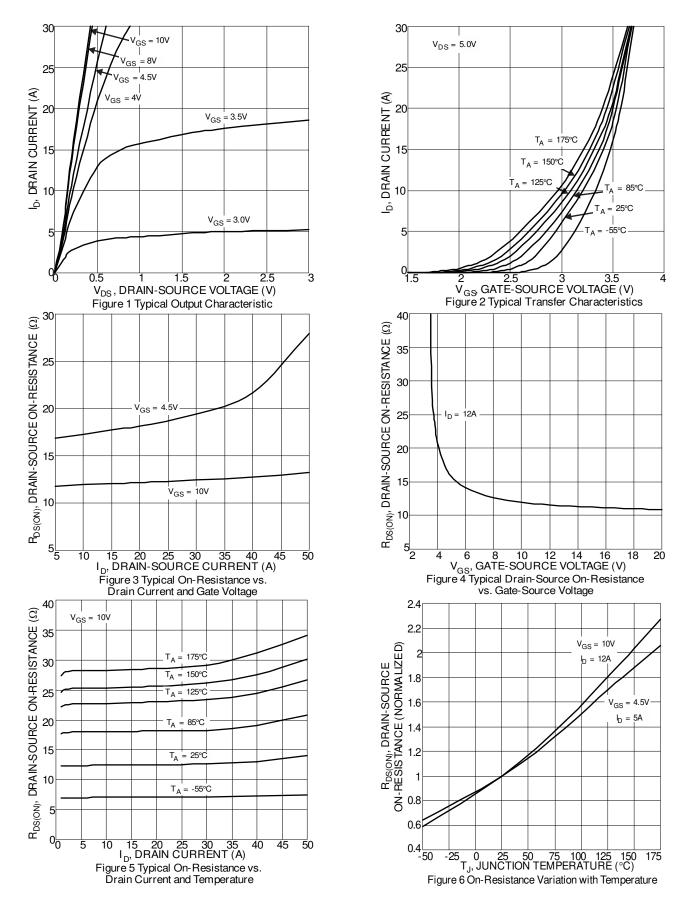
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)						•	
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Б	_	15	25	mΩ	$V_{GS} = 10V, I_D = 15A$	
Static Dialii-Source Oil-nesistance	R _{DS(ON)}	_	21	40		$V_{GS} = 4.5V, I_D = 12A$	
Diode Forward Voltage	V _{SD}	_	0.75	1.2	V	V _{GS} = 0V, I _S = 2.6A	
DYNAMIC CHARACTERISTICS (Note 10)			•	•	•	•	
Input Capacitance	C _{ISS}	_	1,143	_	pF		
Output Capacitance	Coss	_	168	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	69	_	pF I = IMH2		
Gate Resistance	Rg	_	2.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	20.1	_	nC		
Total Gate Charge (V _{GS} = 6V)	Q _G	_	12	_	nC		
Gate-Source Charge	Q _{GS}	_	4.3	_	nC	$V_{DS} = 30V, I_D = 20A,$	
Gate-Drain Charge	Q_{GD}	_	5.5	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	4.4	_	ns		
Turn-On Rise Time	t _R	_	6.0	_	ns	V _{DD} = 30V, V _{GS} = 10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	14.2	_	ns	$R_G = 4.7\Omega$, , $I_D = 20A$	
Turn-Off Fall Time	t _F	_	5.4	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	21.2	_	ns	IE 004 II/II 1004/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	15.2	_	nC	IF=20A, di/dt=100A/μs	

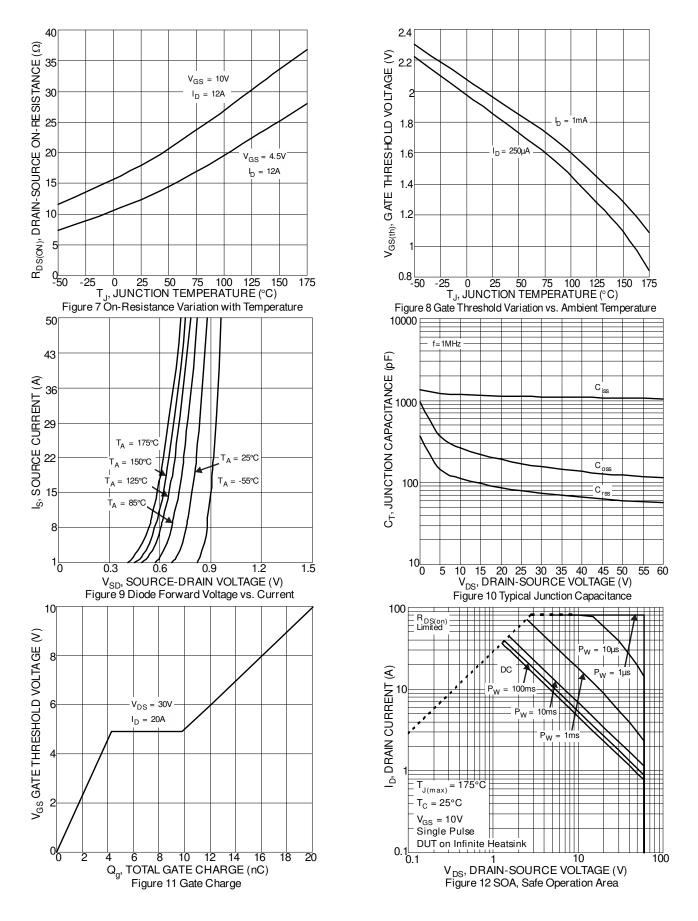
Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. IAS and EAS rating are based on low frequency and duty cycles to keep T_J = 25°C
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

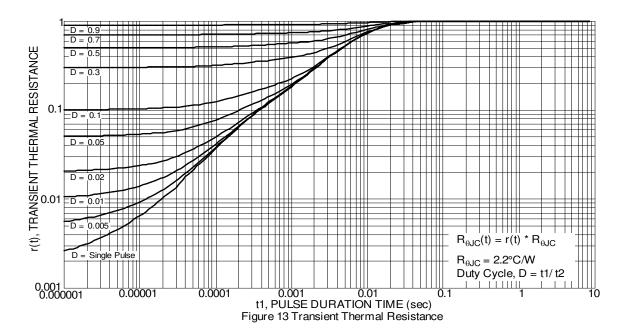










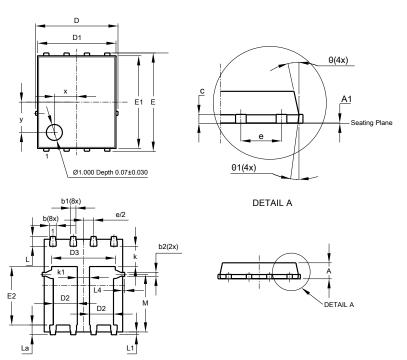




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)

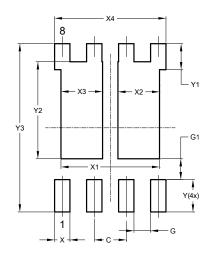


PowerDI5060-8 (Type C)						
Dim	Min Max		Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
C	0.23	0.33	0.277			
D	5	.15 BS	0			
D1	4.85	4.95	4.90			
D2	1.40	1.60	1.50			
D3	1	-	3.98			
Е		6.15 BSC				
E1	5.75	5.85	5.80			
E2	3.56	3.76	3.66			
е	1.27BSC					
k	1	-	1.27			
k1	0.56	-	-			
L	0.51	0.71	0.61			
La	0.51	0.71	0.61			
L1	0.05	0.20	0.175			
L4	1	-	0.125			
М	3.50	3.71	3.605			
x	-	-	1.400			
у	-	-	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

PowerDI5060-8 (Type C)



Dimensions	Value		
Dimensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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